

Super-Junction Power Mosfet

1. Product Information

Features

- Surface-mounted package
- Super Junction technology
- Much lower FOM for fast switching efficiency

Pin Description

Pin	Description
1	Gate(G)
2	Drain(D)
3	Source(S)

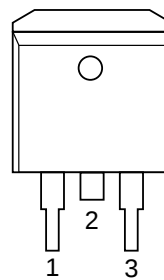
Applications

- Power supply
- Charger
- Solar/UPS-Micro inverter system

Quick reference

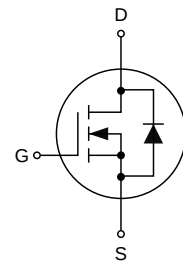
- $V_{DS} \geq 600\text{ V}$
- $I_D \leq 11\text{ A}$
- $R_{DS(ON)} \leq 360\text{ m}\Omega$ @ $V_{GS} = 10\text{ V}$ (Type 330 m Ω)

Simplified Outline



TO-263
Top View

Symbol



Package Marking and Ordering Information

Part number	Marking	Package	Packaging	Quantity	Reel size	Tape width
KJCE60R360D	KJCE60R360D	TO-263	☒ Tape & Reel	800 PCS	13"	24 mm
			☐ Tube	N/A	N/A	N/A

2. Absolute Maximum Ratings (T_C=25°C unless otherwise noted)

Symbol	Parameter	Values	Unit
V_{DS}	Drain-Source Voltage	600	V
V_{GS}	Gate-Source Voltage	±30	V
I_D	Continuous Drain Current (T _C =25°C)	11	A
	Continuous Drain Current (T _C =100°C)	7	A
I_{DM}	Pulsed Drain Current	33	A
E_{AS}	Single Pulsed Avalanche Energy (L=30 mH)	72	mJ
dv/dt	Peak Diode Recovery dv/dt	100	V/ns
I_S	Continuous diode forward current	10	A
P_D	Power Dissipation	104	W
T _J , T _{stg}	Operating Junction and Storage Temperature Range	-55 to 150	°C
$R_{\theta JA}$	Thermal Resistance, Junction-Ambient	100	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction-Case	1.2	°C/W

3. Electrical Characteristics (T_J=25°C, unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Type	Max	Unit
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0 V, I _D =250 μA	600	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =600 V, V _{GS} =0 V	-	-	1	μA
		V _{DS} =600 V, T _C =150°C	-	10	-	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±30 V, V _{DS} =0 V	-	-	±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250 μA	3.0	-	4.0	V
R _{DS(ON)}	Drain-Source On-State Resistance	V _{GS} =10 V, I _D =5.5 A	-	330	360	mΩ
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =100 V, V _{GS} =0 V, f=1 MHz	-	495	-	pF
C _{oss}	Output Capacitance		-	31	-	pF
C _{rss}	Reverse Transfer Capacitance		-	2.4	-	pF
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DS} =400 V, I _D =5.5 A, R _G =27 Ω, V _{GS} =10 V	-	21	-	ns
t _r	Turn-on Rise Time		-	12	-	ns
t _{d(off)}	Turn-off Delay Time		-	72	-	ns
t _f	Turn-off Fall Time		-	13	-	ns
R _g	Gate resistance	f=1 MHz	-	19	-	Ω
Q _g	Total Gate Charge	V _{DS} =400 V, I _D =5.5 A, V _{GS} =10 V	-	38	-	nC
Q _{gs}	Gate-Source Charge		-	6	-	nC
Q _{gd}	Gate-Drain Charge		-	15	-	nC
Source-Drain Diode Characteristics						
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} =0 V, I _F =5.5 A	-	0.9	1.2	V
Q _{rr}	Reverse Recovery Time	V _{DS} =100 V, I _F =5.5 A, di/dt=100 A/μs	-	245	-	μC
T _{rr}	Reverse Recovery Charge		-	3.5	-	ns

4. Electrical Characteristics

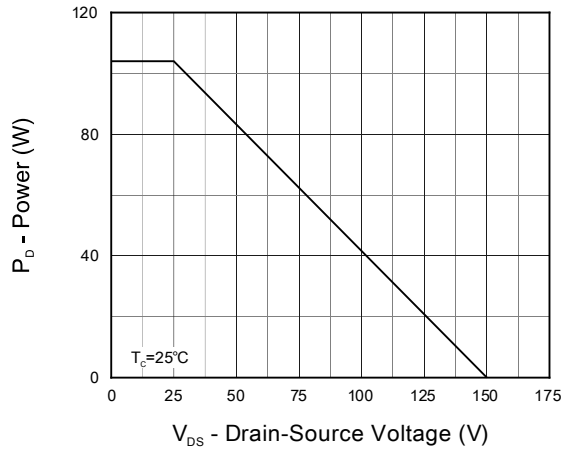


Fig 1. Output Characteristics

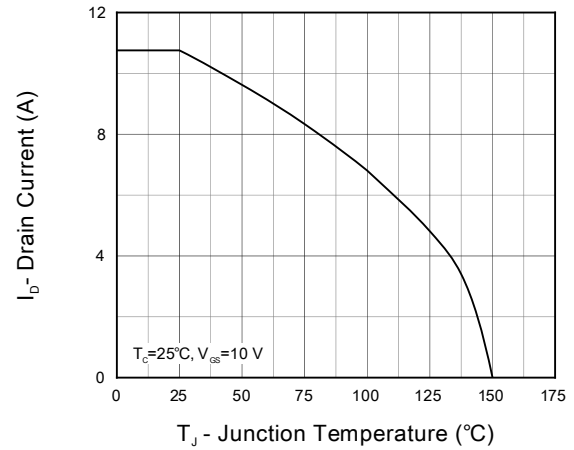


Fig 2. Current Capability

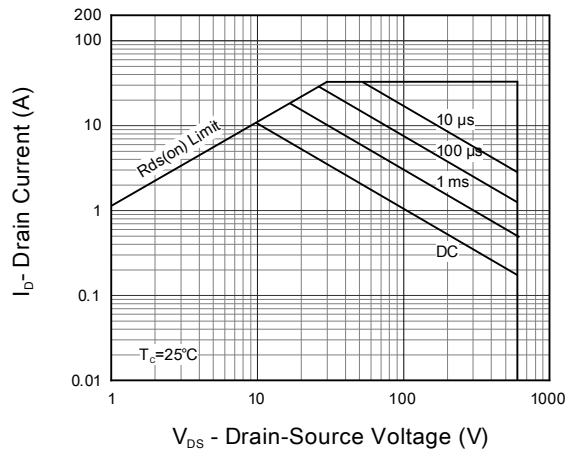


Fig 3. Safe Operation Area

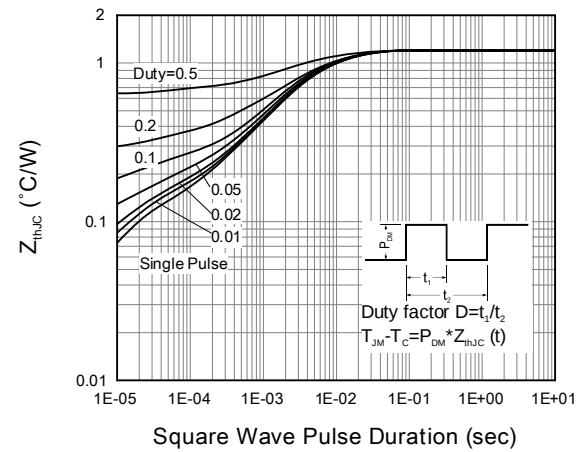


Fig 4. Transient Thermal Impedance

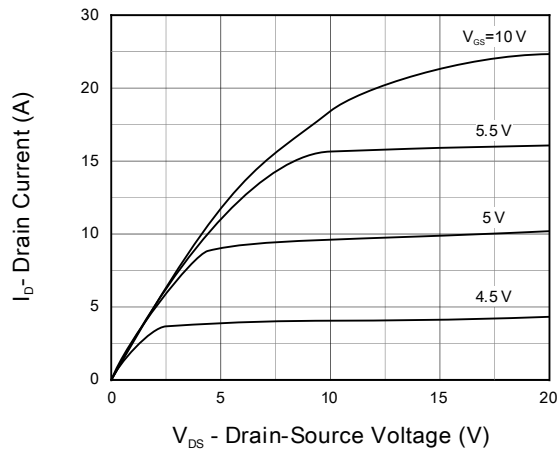


Fig 5. Output Characteristics
 $T_J = 25^\circ\text{C}$

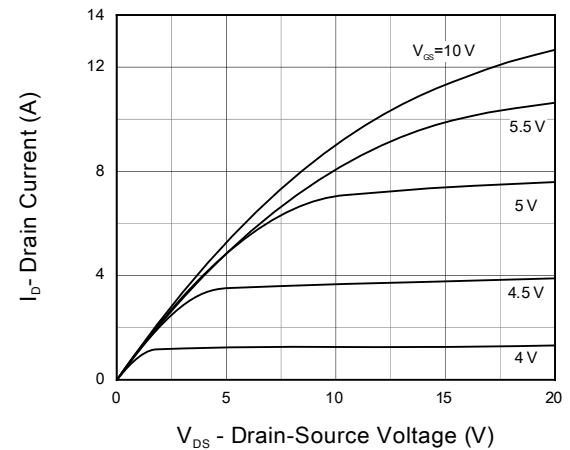
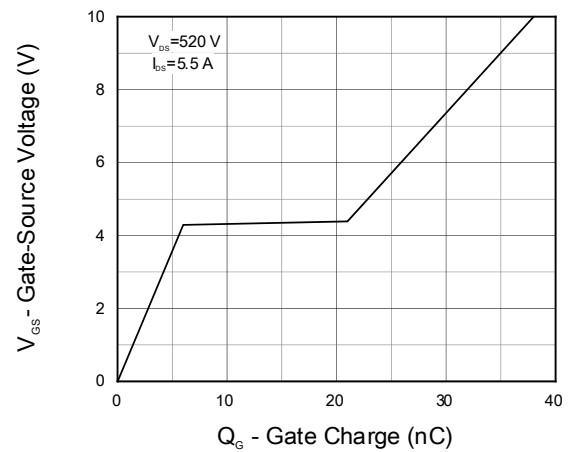
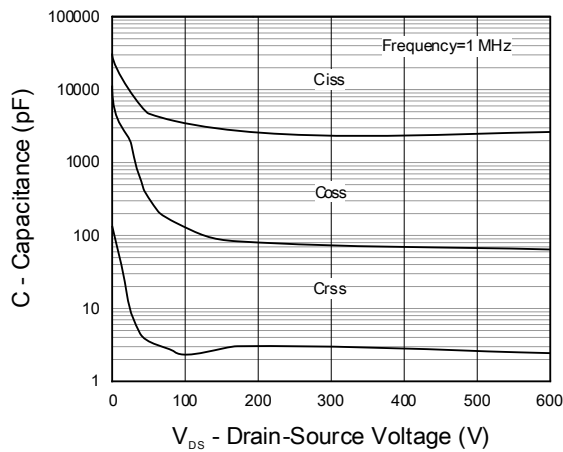
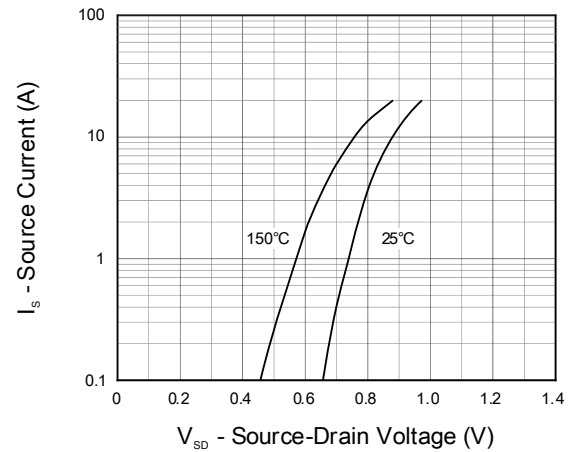
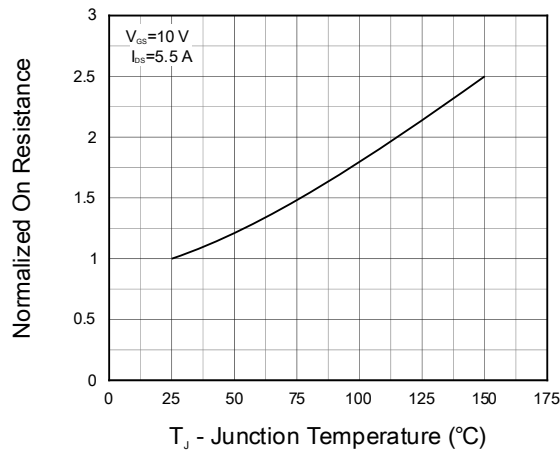
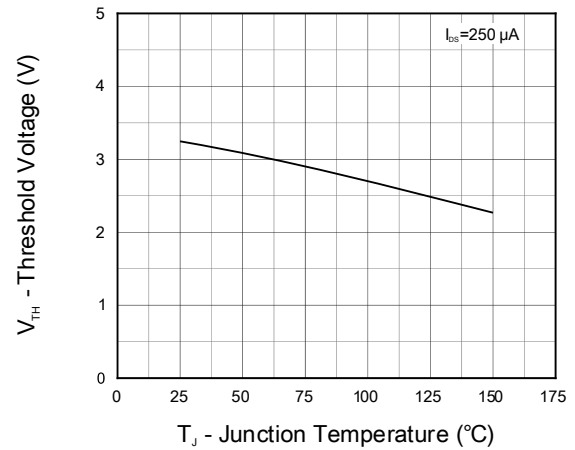
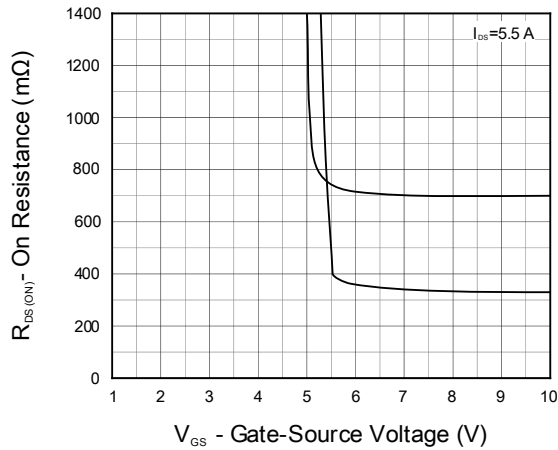


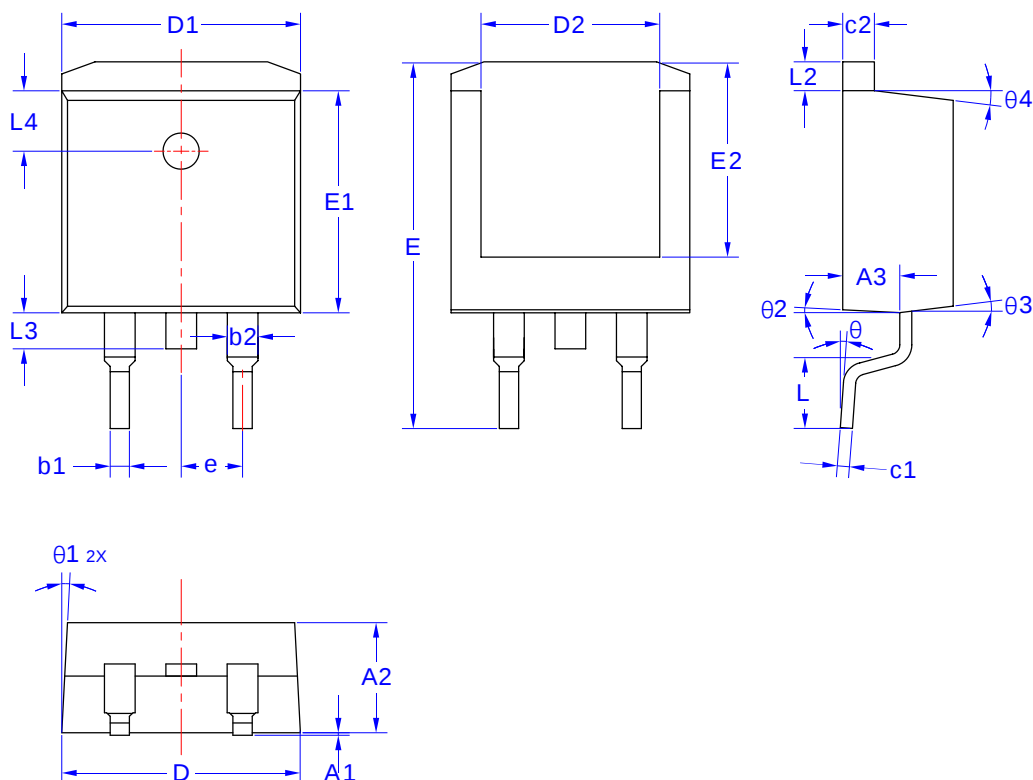
Fig 6. Output Characteristics
 $T_J = 150^\circ\text{C}$

5. Electrical Characteristics (cont.)



5. Package Mechanical Data

TO-263 Package



Symbol	Dimensions in Millimeters		
	MIN	NOM	MAX
A1	0.020	-	0.200
A2	4.470	4.570	4.670
A3	2.300	2.350	2.400
b1	0.750	-	0.850
b2	1.220	-	1.320
c1	0.500	-	0.550
c2	1.300	-	1.350
D	9.780	9.880	9.980
D1		9.880 REF	
D2		7.400 REF	
E	14.900	15.100	15.300
E1	9.100	9.200	9.300

Symbol	Dimensions in Millimeters		
	MIN	NOM	MAX
E2		8.100 REF	
e		5.540 REF	
L	2.100	2.300	2.500
L2	1.025	-	1.375
L3	1.300	1.500	1.700
L4	2.400	2.500	2.600
θ		0-8°	
$\theta 1$		3°	
$\theta 2$		3°	
$\theta 3$		7°	
$\theta 4$		7°	